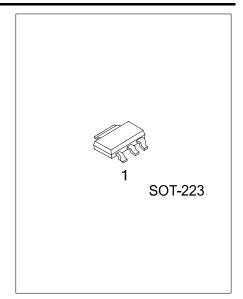


04NM50 Preliminary Power MOSFET

0.4A, 500V N-CHANNEL SUPER-JUNCTION MOSFET

■ DESCRIPTION

The UTC **04NM50** is an Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.



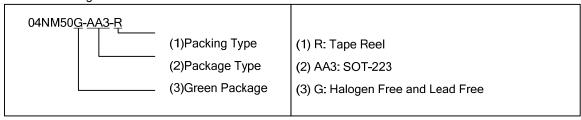
■ FEATURES

- * $R_{DS(on)}$ < 12 Ω @ V_{GS} =10V, I_{D} =0.2A
- * High breakdown voltage

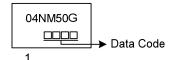
■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Dooking	
		1	2	3	Packing	
04NM50G-AA3-R	SOT-223	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING





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ABSOLUTE MAXIMUM RATINGS (T_C =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	500	V	
Gate-Source Voltage		V_{GSS}	±30	V	
Drain Current	Continuous	I _D	0.4	Α	
	Pulsed	I _{DM}	1.6	Α	
Power Dissipation		P _D	9	W	
Junction Temperature		T_J	150	°C	
Storage Temperature Range		T _{STG}	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	150	°C/W	
Junction to Case	θ_{JC}	14	°C/W	

ELECTRICAL CHARACTERISTICS (T_C =25°C, unless otherwise specified)

PARAMETER		SYMBOL	MBOL TEST CONDITIONS IN		TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV _{DSS}	I_D =250 μ A, V_{GS} =0 V	500			V	
Drain-Source Leakage Current			V _{DS} =500V, V _{GS} =0V			10	μΑ	
Gate-Source Leakage Current	Forward	I _{GSS}	V_{GS} =+30V, V_{DS} =0V			+100	nΑ	
Gate-Source Leakage Current	Reverse		V_{GS} =-30V, V_{DS} =0V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	2.5		4.5	V	
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =0.2A			12	Ω	
DYNAMIC PARAMETERS					1			
Input Capacitance		C _{ISS}			30		pF	
Output Capacitance		Coss	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		25		pF	
Reverse Transfer Capacitance		C _{RSS}			7.5		pF	
SWITCHING PARAMETERS								
Total Gate Charge		Q_{G}	V _{DS} =50V, V _{GS} =10V, I _D =1.3A,		8		nC	
Gate to Source Charge	Gate to Source Charge		1 , ,		2.5		nC	
Gate to Drain Charge		Q_GD	I _D =100μA (Note 1, 2)		3		nC	
Turn-ON Delay Time	_				38		ns	
Rise Time			V_{DS} =30V, V_{GS} =10V, I_{D} =0.5A,		23		ns	
Turn-OFF Delay Time		t _{D(OFF)}	R _G =25Ω (Note 1, 2)		26		ns	
Fall-Time					30		ns	
SOURCE- DRAIN DIODE RATING	GS AND CI	HARACTERI	STICS					
Maximum Body-Diode Continuous	Current	Is				0.4	Α	
Maximum Body-Diode Pulsed Current		I _{SM}				1.6	Α	
Drain-Source Diode Forward Voltage		V_{SD}	I _S =0.4A, V _{GS} =0V			1.4	V	
Notes: 1. Pulse Test: Pulse width:	≤ 300µs, Di	uty cycle≤2%	6.					
2. Essentially independent	of operating	g temperatur	e.					
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			18 188					
			17,60					
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UNISONIC TECHN	OLOGIES	CO., LTD				2 (of 5	
Drain-Source Diode Forward Voltage V _{SD} I _S =0.4A, V _{GS} =0V Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%. 2. Essentially independent of operating temperature. UNISONIC TECHNOLOGIES CO., LTD www.unisonic.com.tw					QW-R205-255.a			

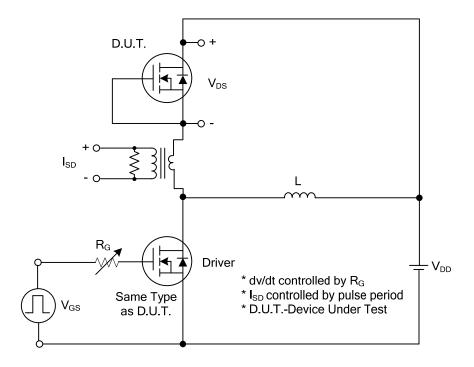
Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle≤2%.



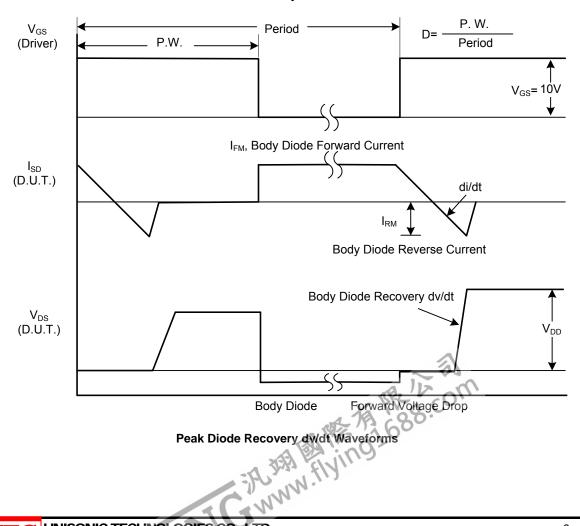
^{2.} Repetitive Rating: Pulse width limited by maximum junction temperature.

^{2.} Essentially independent of operating temperature.

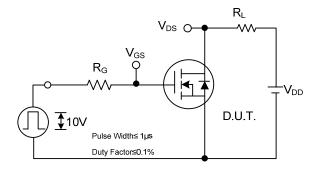
TEST CIRCUITS AND WAVEFORMS

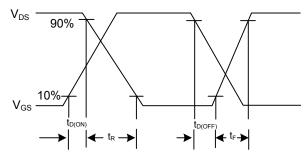


Peak Diode Recovery dv/dt Test Circuit



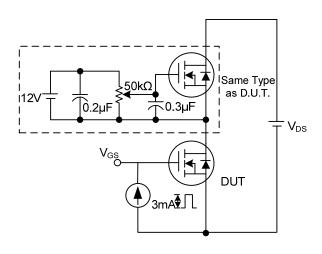
TEST CIRCUITS AND WAVEFORMS (Cont.)

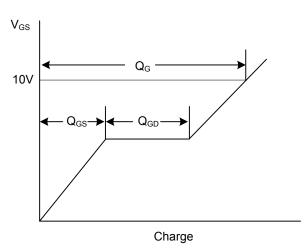




Switching Test Circuit

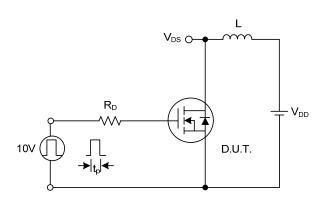
Switching Waveforms

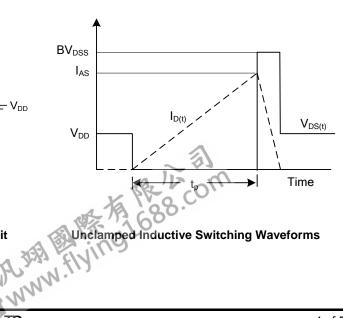




Gate Charge Test Circuit

Gate Charge Waveform





Unclamped Inductive Switching Test Circuit

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